

BTA316B series B, C and E

16 A Three-quadrant triacs high commutation

Rev. 01 — 19 April 2007

Product data sheet

1. Product profile

1.1 General description

Passivated, new generation, high commutation triacs in a SOT404 plastic single-ended surface-mountable package

1.2 Features

- Very high commutation performance maximized at each gate sensitivity
- High immunity to dV/dt

1.3 Applications

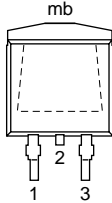

- High power motor control - e.g. washing machines and vacuum cleaners
- Refrigeration and air conditioning compressors
- Non-linear rectifier-fed motor loads
- Electronic thermostats

1.4 Quick reference data

- $V_{DRM} \leq 600$ V (BTA316B-600B/C/E)
- $V_{DRM} \leq 800$ V (BTA316B-800B/C/E)
- $I_{TSM} \leq 140$ A ($t = 20$ ms)
- $I_{T(RMS)} \leq 16$ A ($t = 20$ ms)
- $I_{GT} \leq 50$ mA (BTA316B series B)
- $I_{GT} \leq 35$ mA (BTA316B series C)
- $I_{GT} \leq 10$ mA (BTA316B series E)

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	main terminal 1 (T1)		
2	main terminal 2 (T2)		
3	gate (G)		
mb	mounting base; main terminal 2 (T2)		

SOT404 (D2PAK)

3. Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
BTA316B-600B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3-leads (one lead cropped)	SOT404
BTA316B-600C			
BTA316B-600E			
BTA316B-800B			
BTA316B-800C			
BTA316B-800E			

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V _{DRM}	repetitive peak off-state voltage	BTA316B-600B; BTA316B-600C; BTA316B-600E	[1]	-	600	V
		BTA316B-800B; BTA316B-800C; BTA316B-800E	-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 101 °C; see Figure 4 and 5	-	16	A	
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _j = 25 °C prior to surge; see Figure 2 and 3	-	-	-	
		t = 20 ms	-	140	A	
		t = 16.7 ms	-	150	A	
I ² t	I ² t for fusing	t = 10 ms	-	98	A ² s	
di _T /dt	rate of rise of on-state current	I _{TM} = 20 A; I _G = 0.2 A; di _G /dt = 0.2 A/μs	-	100	A/μs	
I _{GM}	peak gate current		-	2	A	
P _{GM}	peak gate power		-	5	W	
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W	
T _{stg}	storage temperature		-40	+150	°C	
T _j	junction temperature		-	125	°C	

[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/μs.

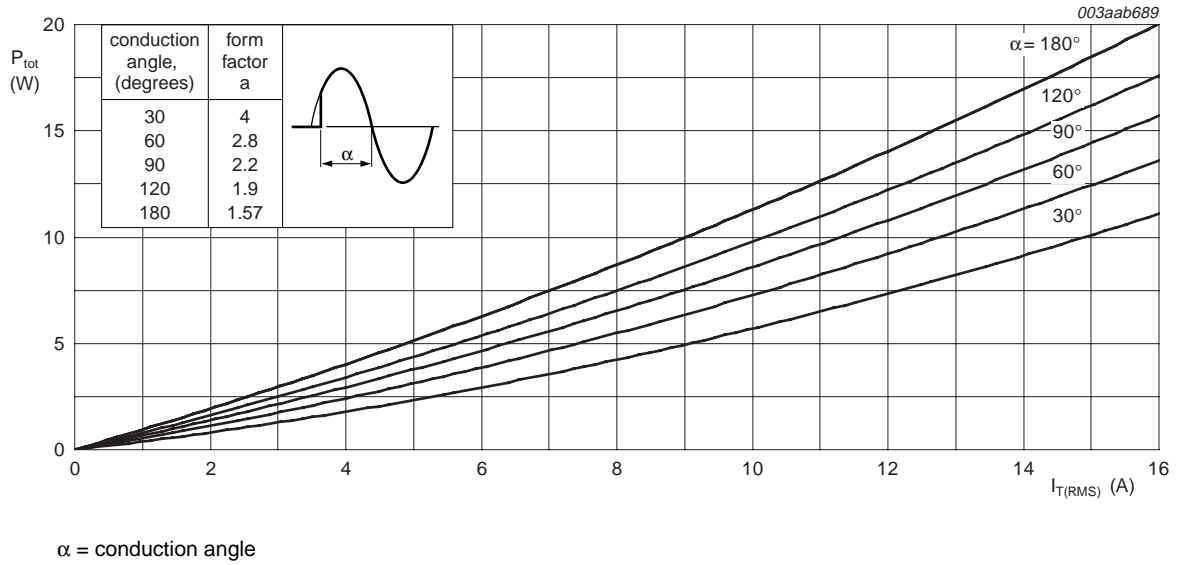


Fig 1. Total power dissipation as a function of RMS on-state current; maximum values

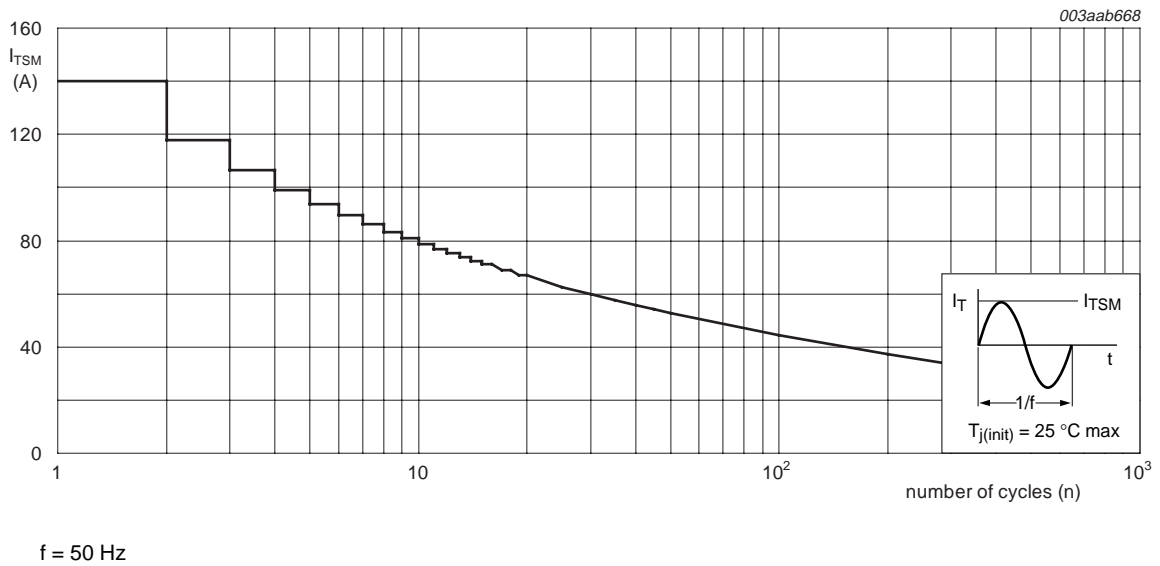
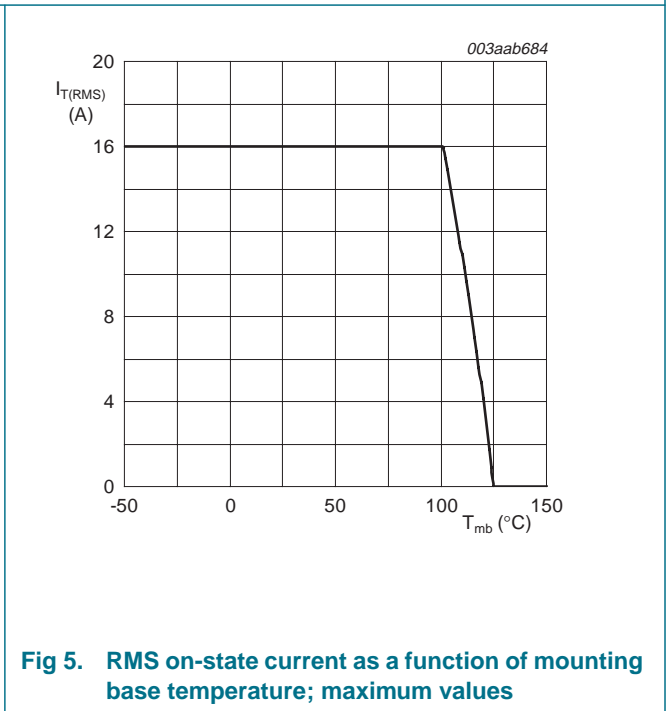
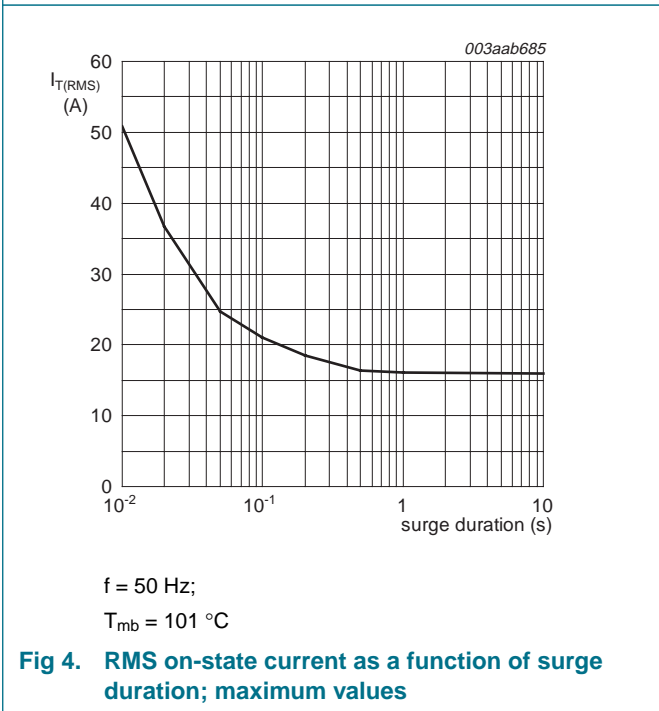
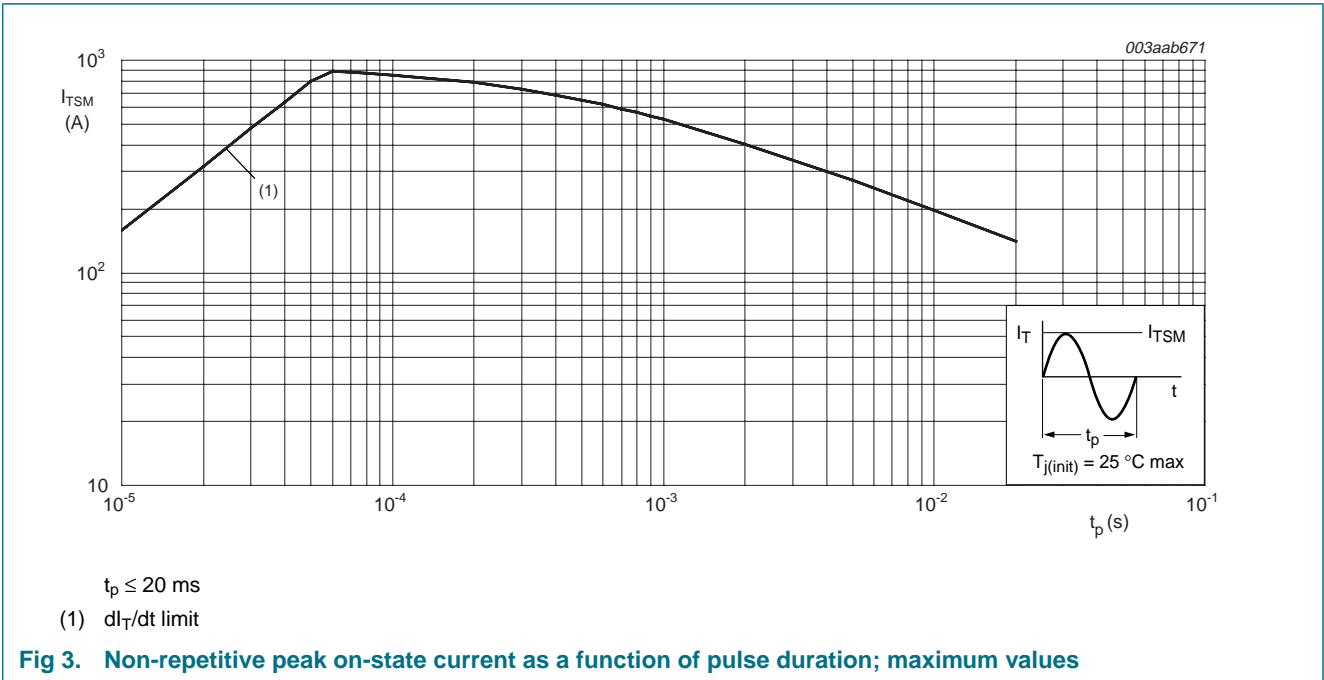


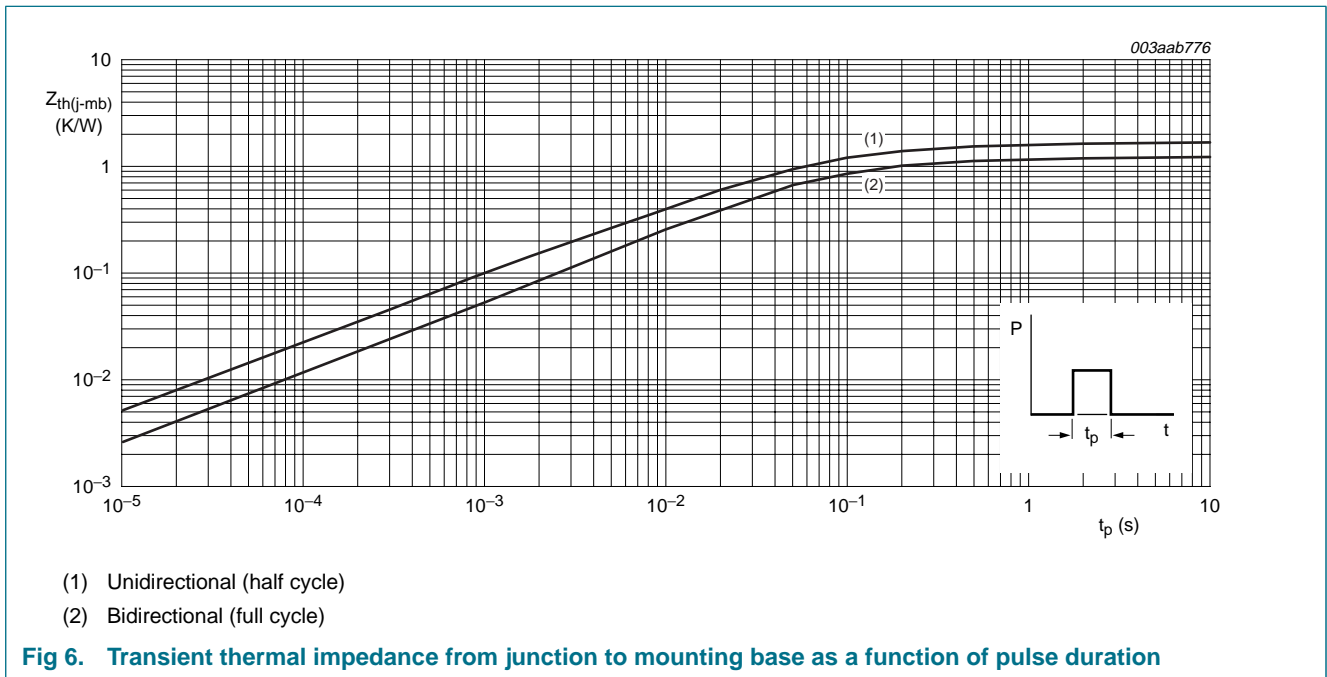
Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	half cycle; see Figure 6	-	-	1.7	K/W
		full cycle; see Figure 6	-	-	1.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on a printed circuit board; minimum footprint	-	55	-	K/W



6. Static characteristics

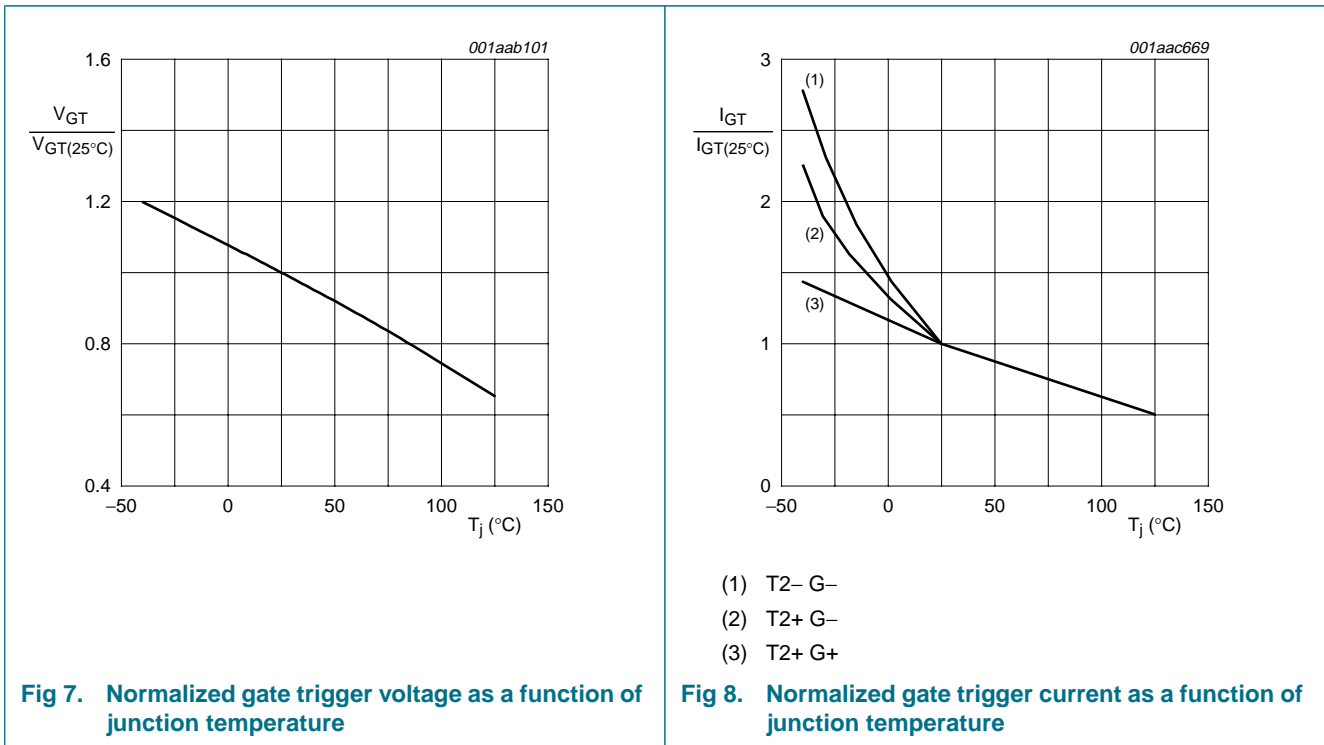
Table 5. Static characteristics
T_j = 25 °C unless otherwise specified.

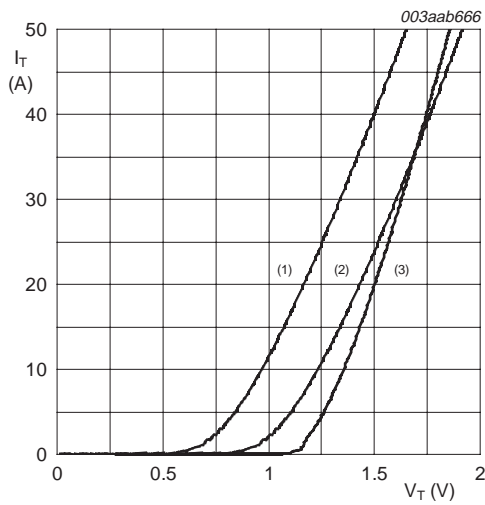
Symbol	Parameter	Conditions	BTA316B-600B BTA316B-800B			BTA316B-600C BTA316B-800C			BTA316B-600E BTA316B-800E			Unit	
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max		
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; see Figure 8											
			T2+ G+	2	-	50	2	-	35	-	-	10	mA
			T2+ G-	2	-	50	2	-	35	-	-	10	mA
			T2- G-	2	-	50	2	-	35	-	-	10	mA
I _L	latching current	V _D = 12 V; I _{GT} = 0.1 A; see Figure 10											
			T2+ G+	-	-	60	-	-	50	-	-	25	mA
			T2+ G-	-	-	90	-	-	60	-	-	30	mA
			T2- G-	-	-	60	-	-	50	-	-	30	mA
I _H	holding current	V _D = 12 V; I _{GT} = 0.1 A; see Figure 11	-	-	60	-	-	35	-	-	15	mA	
V _T	on-state voltage	I _T = 18 A; see Figure 9	-	1.3	1.5	-	1.3	1.5	-	1.3	1.5	V	
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; see Figure 7	-	0.8	1.5	-	0.8	1.5	-	0.8	1.5	V	
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C	0.25	0.4	-	0.25	0.4	-	0.25	0.4	-	V	
I _D	off-state current	V _D = V _{DRM(max)} ; T _j = 125 °C	-	0.1	0.5	-	0.1	0.5	-	0.1	0.5	mA	

7. Dynamic characteristics

Table 6. Dynamic characteristics

Symbol	Parameter	Conditions	BTA316B-600B BTA316B-800B			BTA316B-600C BTA316B-800C			BTA316B-600E BTA316B-800E			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)}$; $T_j = 125\text{ }^\circ\text{C}$; exponential waveform; gate open circuit	1000	-	-	500	-	-	60	-	-	V/ μs
di_{com}/dt	rate of change of commutating current	$V_{DM} = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 16\text{ A}$; without snubber; gate open circuit	20	-	-	15	-	-	5	-	-	A/ms
		$V_{DM} = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 16\text{ A}$; $dV/dt = 10\text{ V}/\mu\text{s}$; gate open circuit	-	-	-	-	-	-	8	-	-	A/ms
		$V_{DM} = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 16\text{ A}$; $dV/dt = 1\text{ V}/\mu\text{s}$; gate open circuit	-	-	-	-	-	-	12	-	-	A/ms
t_{gt}	gate-controlled turn-on time	$I_{TM} = 20\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1\text{ A}$; $di_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	-	2	-	-	2	-	μs





$V_o = 1.024 \text{ V}$

$R_s = 0.021 \text{ } \Omega$

- (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
- (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig 9. On-state current as a function of on-state voltage

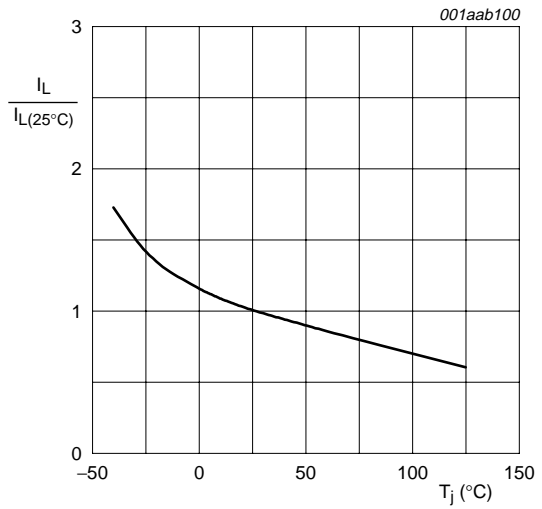


Fig 10. Normalized latching current as a function of junction temperature

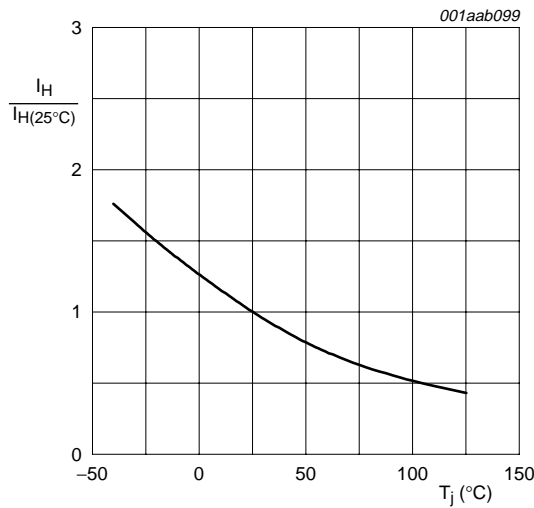
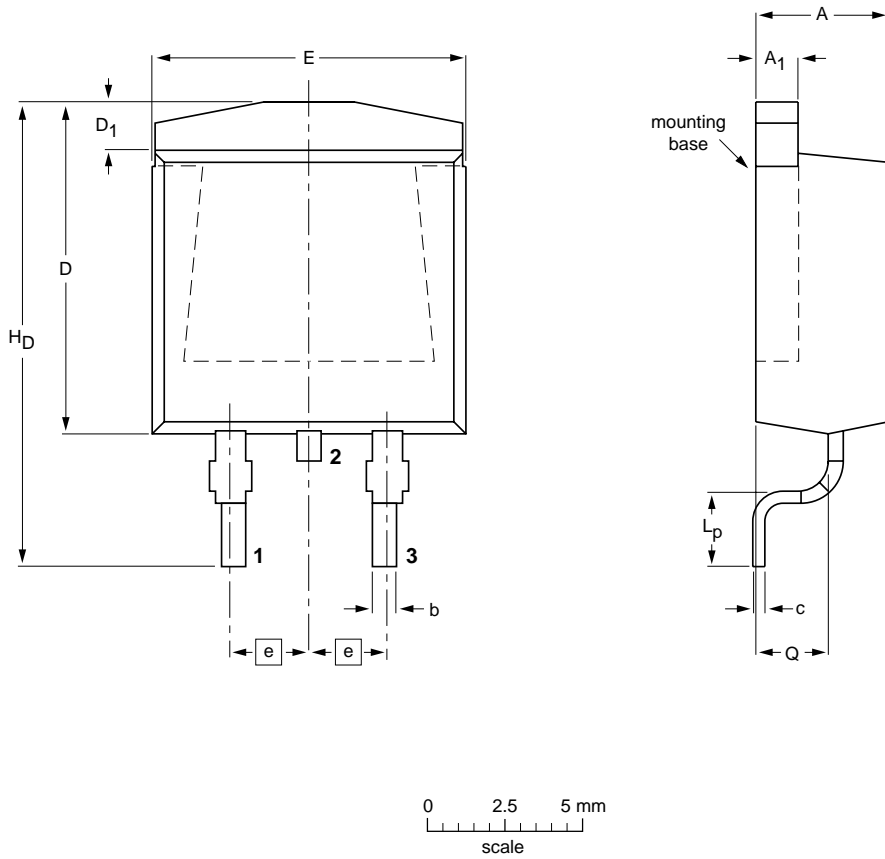


Fig 11. Normalized holding current as a function of junction temperature

8. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	c	D max.	D ₁	E	e	L _p	H _D	Q
mm	4.50	1.40	0.85	0.64	11	1.60	10.30	2.54	2.90	15.80	2.60
	4.10	1.27	0.60	0.46		1.20	9.70		2.10	14.80	2.20

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT404						05-02-11 06-03-16

Fig 12. Package outline SOT404 (D2PAK)

9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA316B_SER_B_C_E_1	20070419	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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